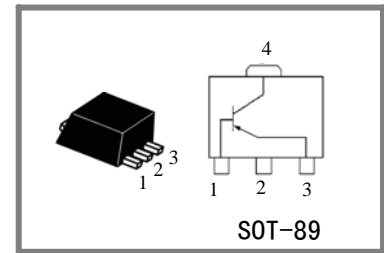


## PNP-Silicon General use Transistors

1W、1.0A、25V



1 Base 2/4 Collector 3 Emitter

**Applications:** Can be used for switching and amplifying in various electrical and electronic circuit.

### Maximum ratings

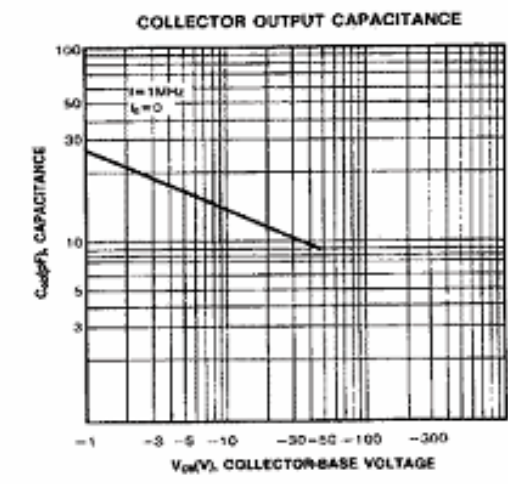
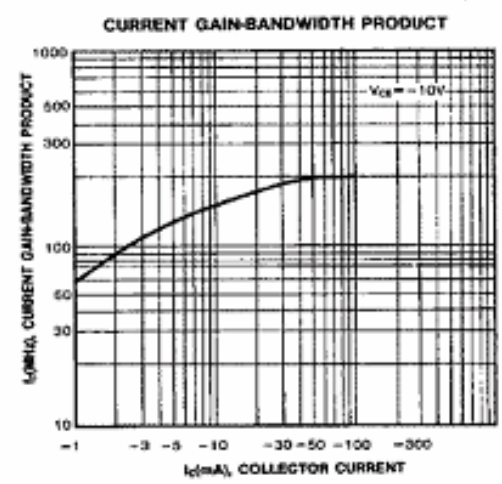
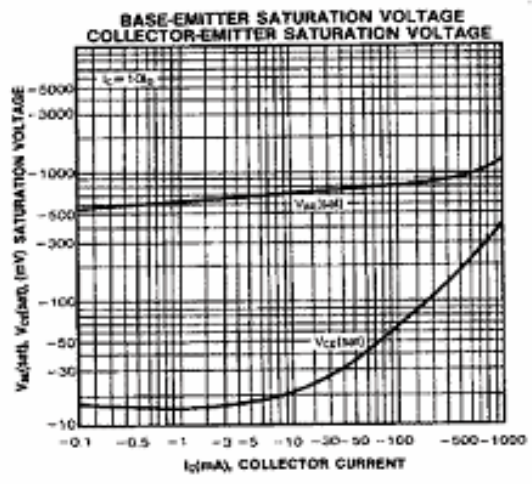
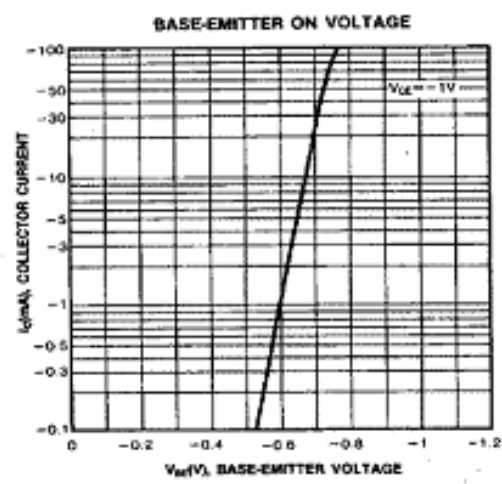
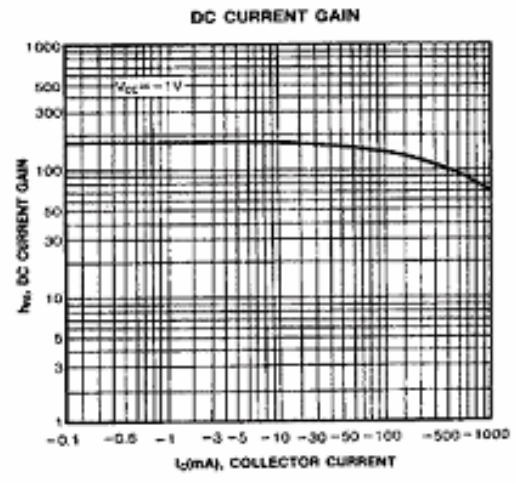
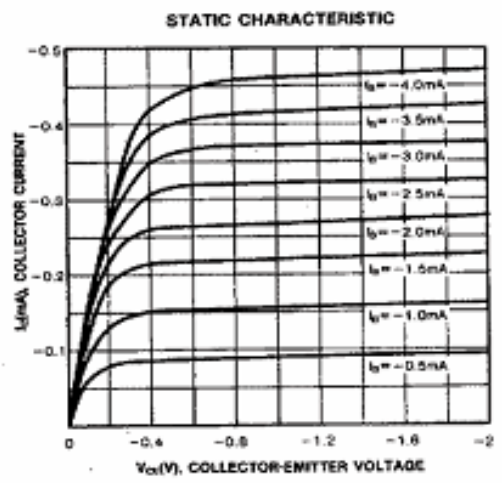
Parameters	Symbol	Rating	Unit
Collector-emitter voltage ( $I_B=0$ )	$V_{CEO}$	25	V
Collector-base voltage ( $I_E=0$ )	$V_{CBO}$	30	V
Emitter-base voltage ( $I_C=0$ )	$V_{EBO}$	6	V
Collector current	$I_C$	1.0	A
Total dissipation power( $T_A=25^\circ\text{C}$ )*	$P_{tot}$	1	W
Junction temperature	$T_{jm}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

\* Device is mounted on a printed circuit board.

### Electrical characteristics (Unless otherwise specified, $T_A=25^\circ\text{C}$ )

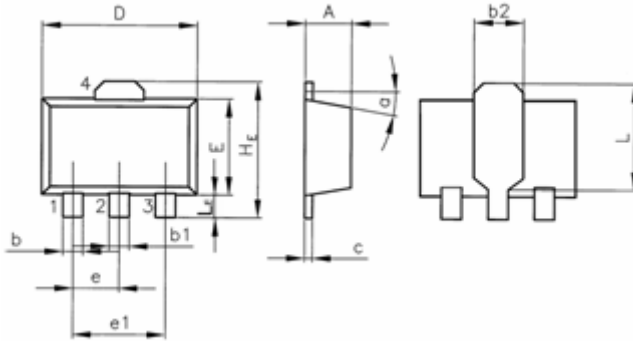
Parameters		Symbol	Test condition	Min.	Max.	Unit
Collector-emitter breakdown voltage		$V_{(BR)CEO}$	$I_C=2\text{mA}$ , $I_B=0$	25	—	V
Collector-base breakdown voltage		$V_{(BR)CBO}$	$I_C=100\mu\text{A}$ , $I_E=0$	30	—	V
Emitter-base breakdown voltage		$V_{(BR)EBO}$	$I_E=100\mu\text{A}$ , $I_C=0$	6	—	V
Forward current transfer ratio	DL	$h_{FE}$	$V_{CE}=1\text{V}$ ; $I_C=100\text{mA}$	135	270	—
	DK			200	400	—
Collector-base current		$I_{CBO}$	$V_{CB}=35\text{V}$ , $I_E=0$	—	100	nA
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C=800\text{mA}$ , $I_B=80\text{mA}$	—	0.5	V
Characteristic frequency		$f_T$	$I_C=50\text{mA}$ , $V_{CE}=10\text{V}$ , $f=100\text{MHz}$	200	—	MHz

## Typical characteristics



Outline dimensions (see fig.1)

Unit: mm



Dimensions Symbol	SOT-89		
	min	type	max
A	1.4		1.6
b	0.35		0.55
b1	0.4		0.65
b2		1.6	
c	0.35		0.45
D	4.4		4.6
E	2.35		2.55
e		1.5	
e1		3	
HE		4.15	
L		2.7	
LE		1.0	
a		5°	

Fig.1 Outline Dimensions